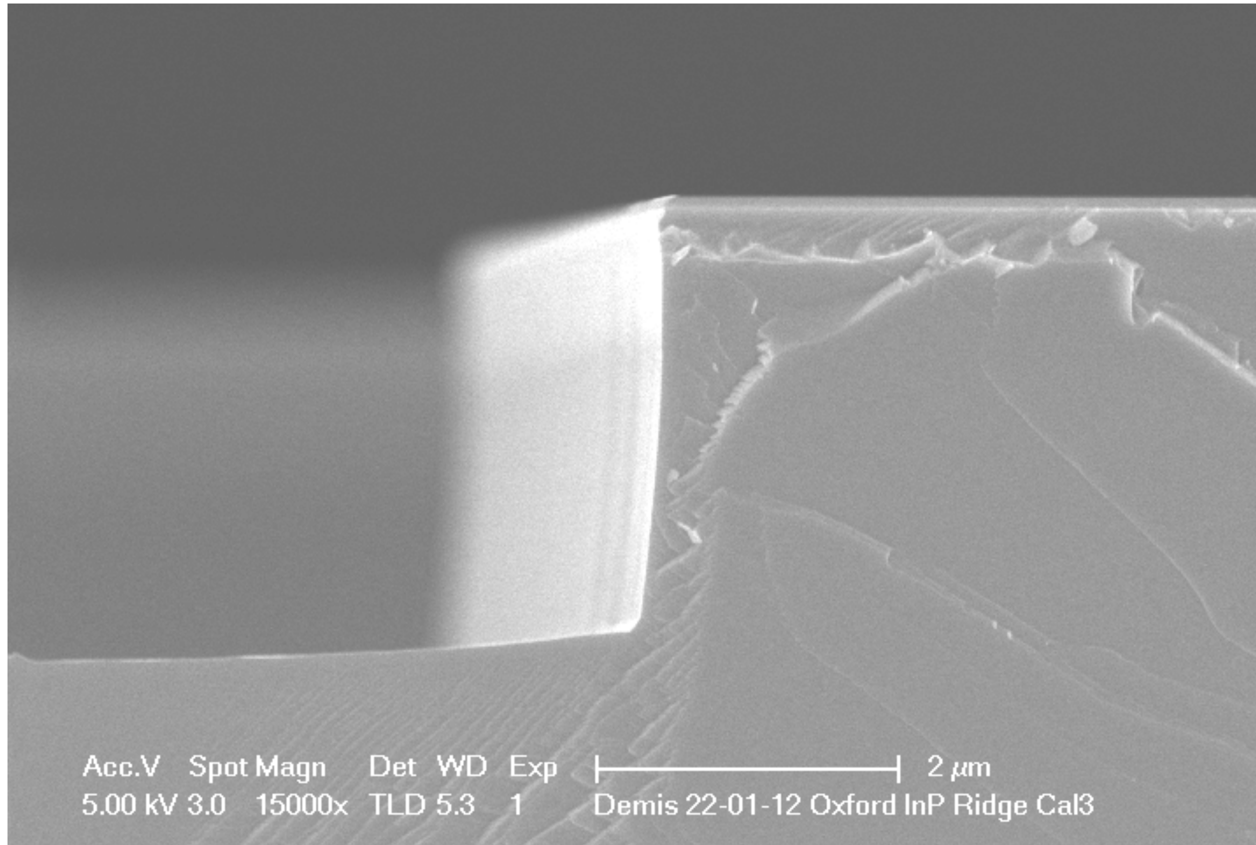
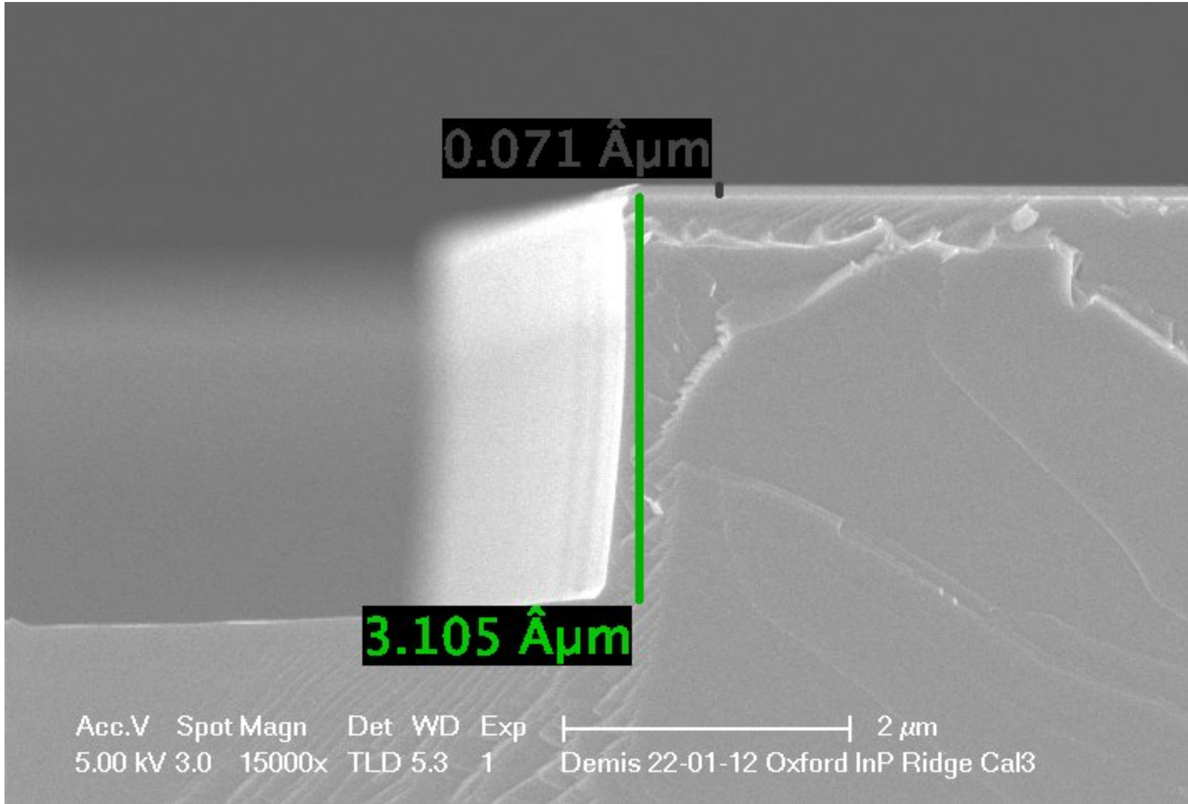
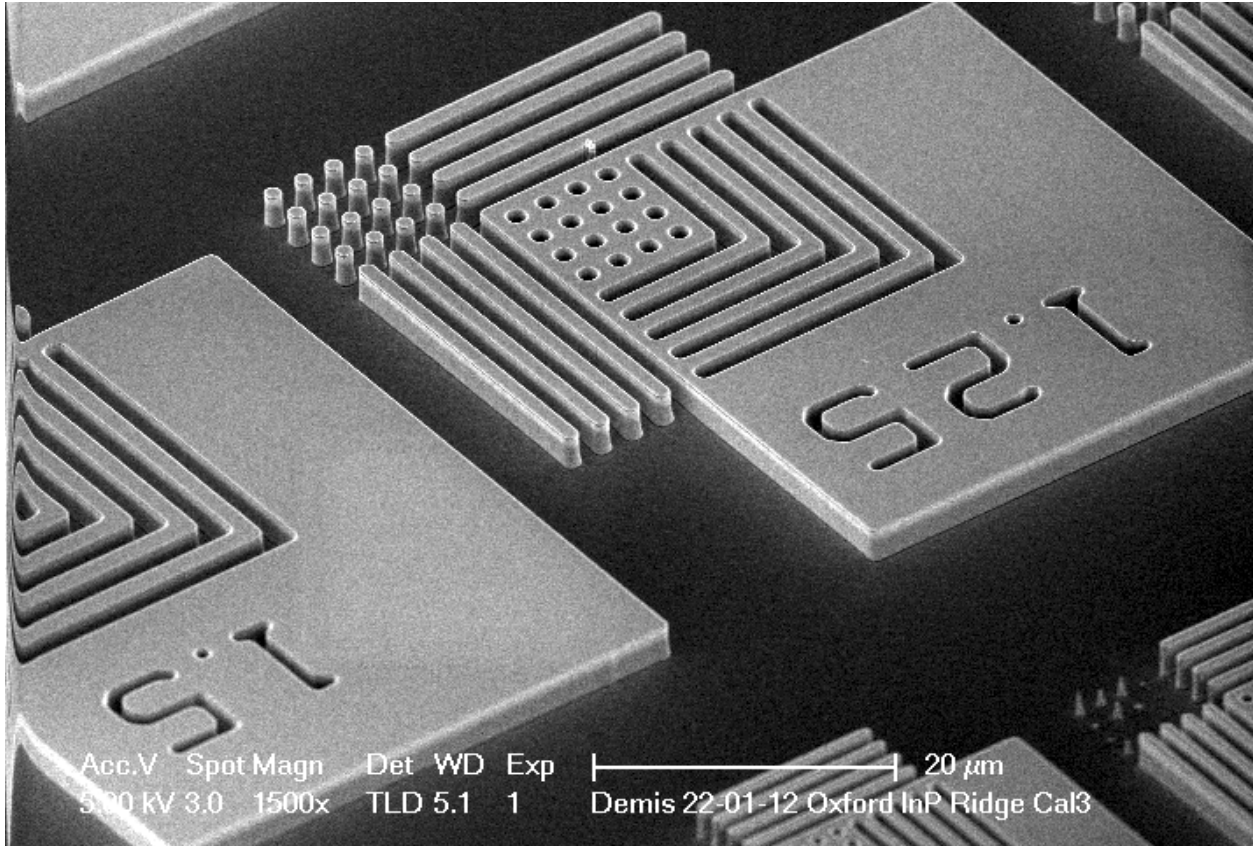
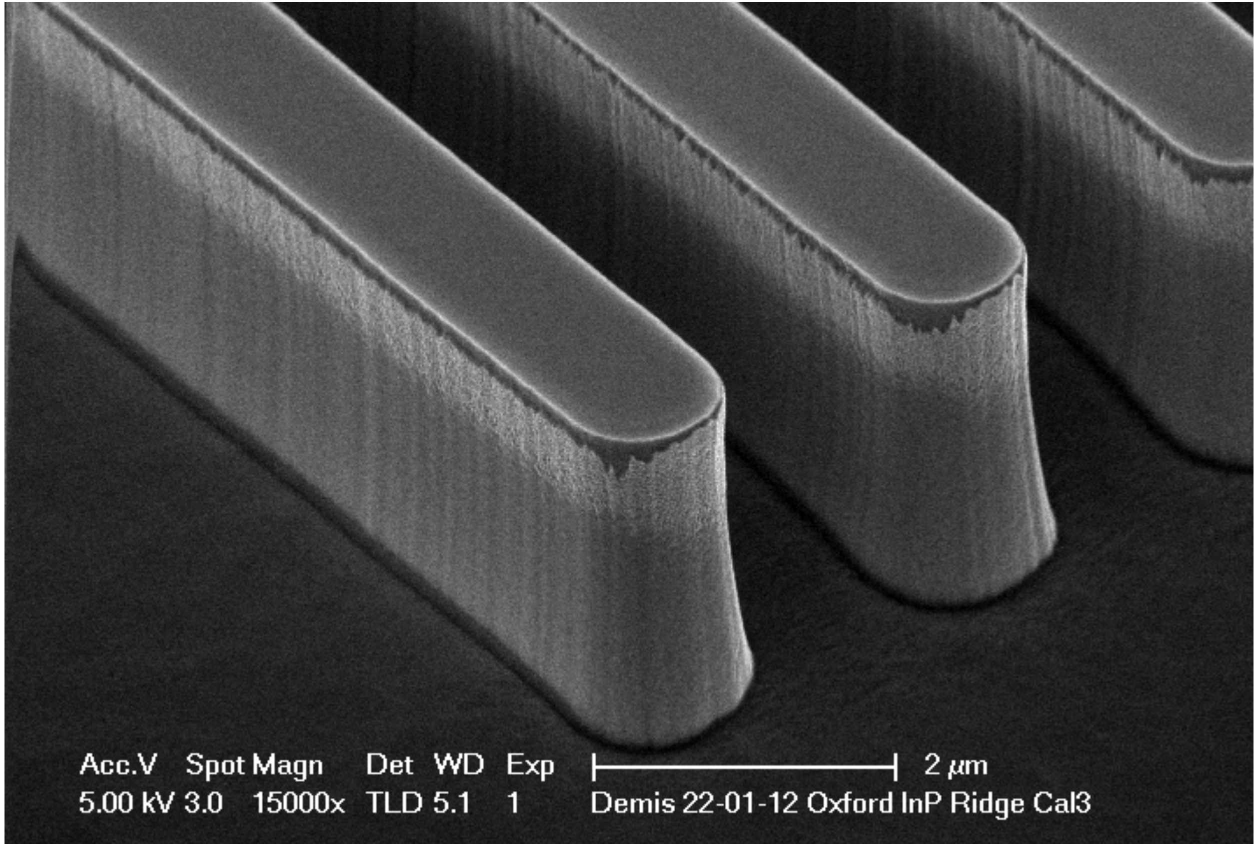
2022-01-12 DJ Cal – InP Ridge Process
Ning's "InP Wafer" patterned samples
Oxford ICP "InP Ridge Etch":
3mT, 800W/65W, Cl2=18, H2=15, CH4=10sccm, time=5min05sec (305sec)

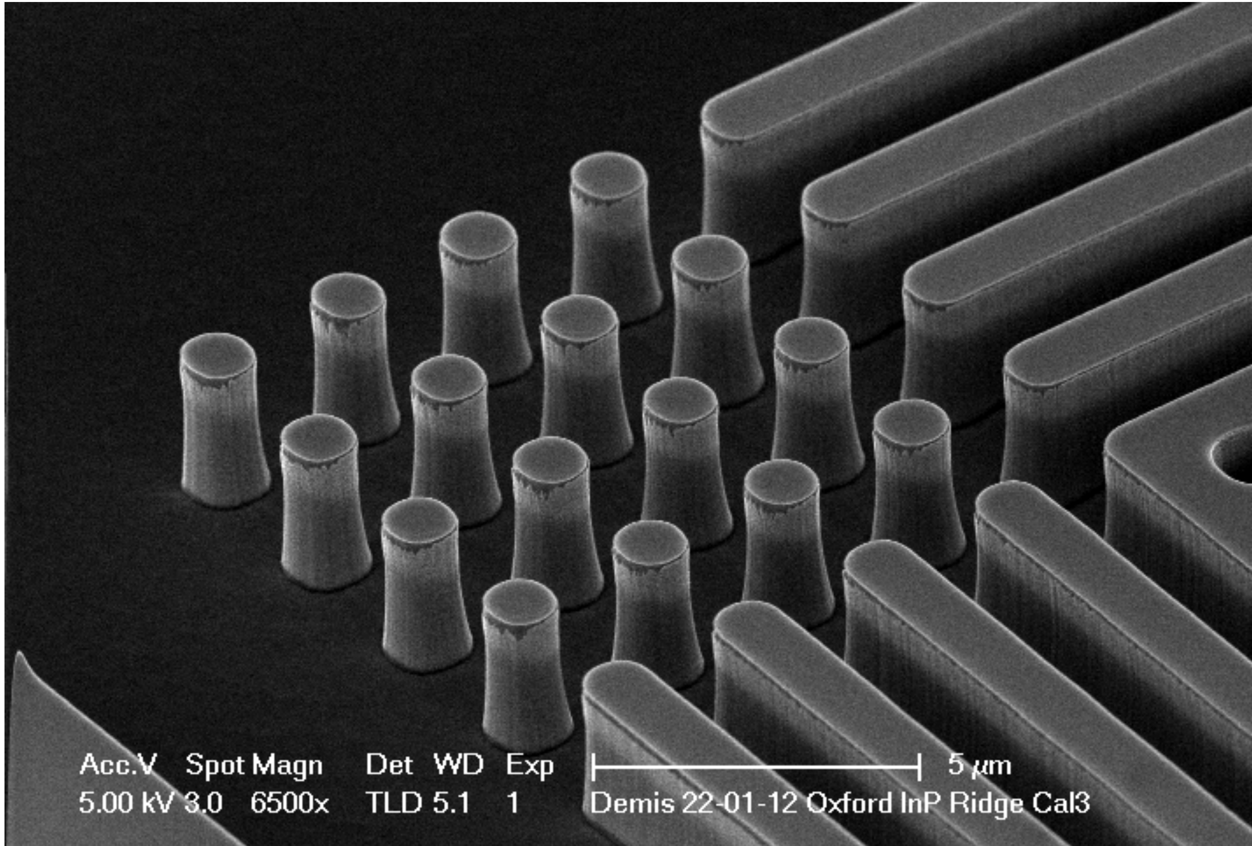



0.071 Âµm
3.105 Âµm
Acc.V Spot Magn Det WD Exp
5.00 kV 3.0 15000x TLD 5.3 1
2 µm
Demis 22-01-12 Oxford InP Ridge Cal3


Acc.V Spot Magn Det WD Exp
5.00 kV 3.0 1500x TLD 5.1 1
20 μm
Demis 22-01-12 Oxford InP Ridge Cal3



Top corners etched due to high ion bombardment from SiO2 hardmask charging


Acc.V Spot Magn Det WD Exp
5 μm
5.00 kV 3.0 6500x TLD 5.1 1
Demis 22-01-12 Oxford InP Ridge Cal3